

L Number	Hits	Search Text	DB	Time stamp
1	14	(group adj (III adj V) adj compound adj semiconductor) with nitride with (group adj III adj element)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/22 09:07
2	14	mask with (longitudinal adj direction) with degrees	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/22 09:14
3	0	thickness adj mask adj greater adj than adj opening	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/22 09:15
4	0	(thickness adj mask) with (greater adj than) with opening	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/22 09:18
5	0	(thickness adj mask) same (greater adj than) same opening	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/22 09:15
6	0	(thickness adj mask) same (greater adj than)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/22 09:16
7	0	(thickness adj mask) with (greater adj than)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/22 09:16
8	0	(mask adj thickness) with (greater adj than)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/22 09:17
9	110	(mask adj thicker)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/22 09:17
10	0	(mask adj thicker) adj than adj opening	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/22 09:17
11	0	(mask adj thicker) adj than	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/22 09:17
12	0	(mask adj thicker) adj opening	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/22 09:18
13	4	(mask adj thicker) with opening	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/22 09:18
14	148	(thickness adj mask) with opening	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/22 09:19

15	0	(thickness adj mask) with opening with stripe	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/22 09:20
16	3	(thickness adj mask) same opening same stripe	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/22 11:05
-	1447	mask with (base adj material) wity (III adj V adj epitaxial adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/18 08:25
-	0	mask with (base adj material) with (III adj V adj epitaxial adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/18 08:26
-	0	mask with (III adj V adj epitaxial adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/18 09:34
-	723	(gan or (gallium adj nitride)) and (epitaxial adj growth) and dislocations	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/18 09:52
-	377	(gan or (gallium adj nitride)) and (epitaxial adj growth) and dislocations and mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/18 14:06
-	8	(gan or (gallium adj nitride)) adj film adj masks	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/18 14:27
-	23	(gan or (gallium adj nitride)) adj layer adj masks	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/18 14:40
-	0	(gan or (gallium adj nitride)) adj (region or portion) adj masks	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/18 14:41
-	42	(gan or (gallium adj nitride)) adj masks	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/19 08:24
-	1	6225650.pn. and facet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/22 09:01